

74LVC16240A

16-bit buffer/line driver with 5 V tolerant inputs/outputs;
inverting; 3-state

Rev. 03 — 5 March 2004

Product data sheet

1. General description

The 74LVC16240A is a high-performance, low power, low voltage, Si-gate CMOS device, superior to most advanced CMOS compatible TTL families. Inputs can be driven from either 3.3 V or 5 V devices. In 3-state operation, outputs can handle 5 V. These features allow the use of these devices as a mixed 3.3 V and 5 V environment.

The 74LVC16240A is a 16-bit inverting buffer/line driver with 3-state outputs. The device can be used as four 4-bit buffers, two 8-bit buffers or one 16-bit buffer. The device features four output enables ($1\overline{OE}$, $2\overline{OE}$, $3\overline{OE}$ and $4\overline{OE}$), each controlling four of the 3-state outputs. A HIGH on \overline{OE} causes the outputs to assume a high-impedance OFF-state.

This device is fully specified for partial power-down applications using I_{off} . The I_{off} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

The 74LVC16240A is identical to the 74LVC16244A but has inverting outputs.

2. Features

- 5 V tolerant inputs/outputs for interfacing with 5 V logic
- Wide supply voltage range from 1.2 V to 3.6 V
- CMOS low power consumption
- MULTIBYTE flow-through standard pin-out architecture
- Low inductance multiple power and ground pins for minimum noise and ground bounce
- Direct interface with TTL levels
- Complies with JEDEC standard no. 8-1 A
- ESD protection:
 - ◆ HBM EIA/JESD22-A114-A exceeds 2 000 V
 - ◆ MM EIA/JESD22-A115-A exceeds 200 V.
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$.

PHILIPS

3. Quick reference data

Table 1: Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_{PHL} , t_{PLH}	propagation delay nAn to nYn	$C_L = 50$ pF; $V_{CC} = 3.3$ V	1.0	2.8	4.2	ns
t_{PZH} , t_{PZL}	3-state output enable time nOE to nYn	$C_L = 50$ pF; $V_{CC} = 3.3$ V	1.0	3.5	5.0	ns
t_{PHZ} , t_{PLZ}	3-state output disable time nOE to nYn	$C_L = 50$ pF; $V_{CC} = 3.3$ V	1.5	3.9	4.9	ns
C_I	input capacitance		-	5.0	-	pF
C_{PD}	power dissipation capacitance per gate	$V_{CC} = 3.3$ V outputs enabled outputs disabled	[1] [2] - -	12 4.0	- -	pF pF

[1] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = total load switching outputs;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

[2] The condition is $V_I = \text{GND to } V_{CC}$.

4. Ordering information

Table 2: Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
74LVC16240ADGG	-40 °C to +125 °C	TSSOP48	plastic thin shrink small outline package; 48 leads; body width 6.1 mm	SOT362-1
74LVC16240ADL	-40 °C to +125 °C	SSOP48	plastic shrink small outline package; 48 leads; body width 7.5 mm	SOT370-1

5. Functional diagram

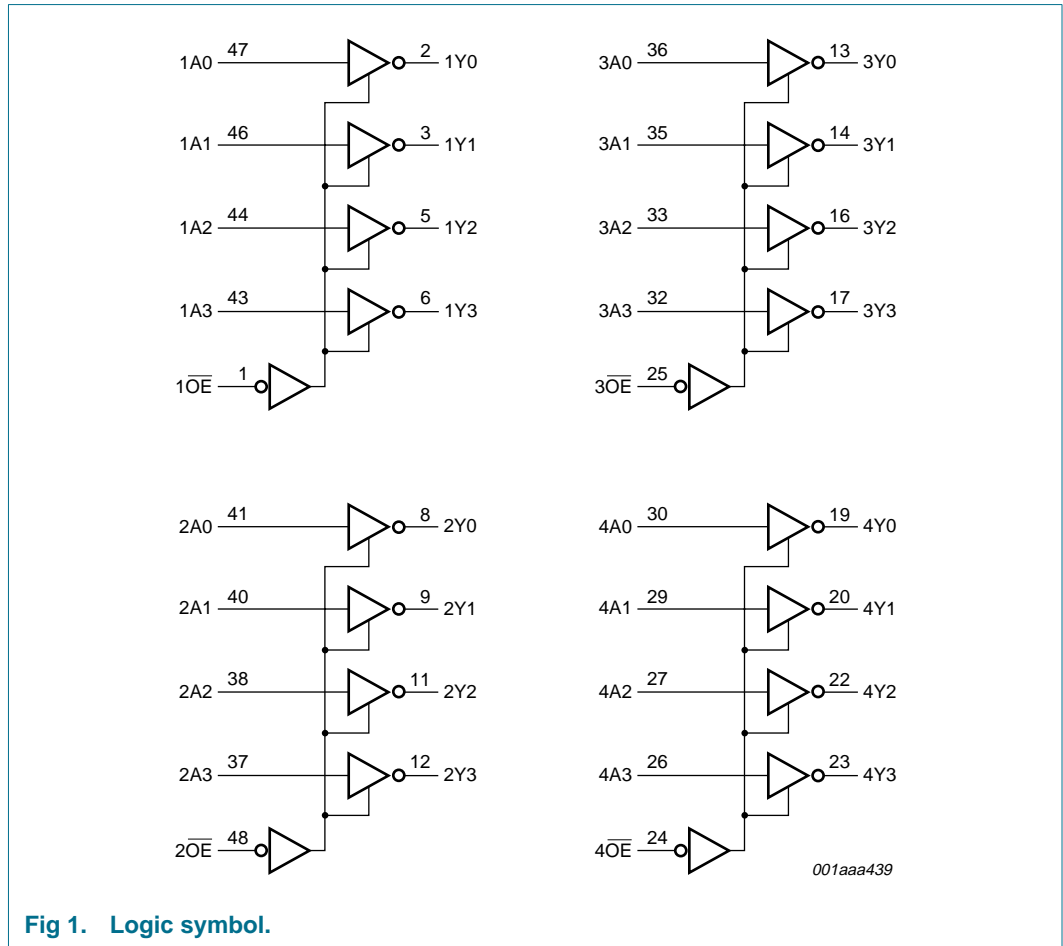
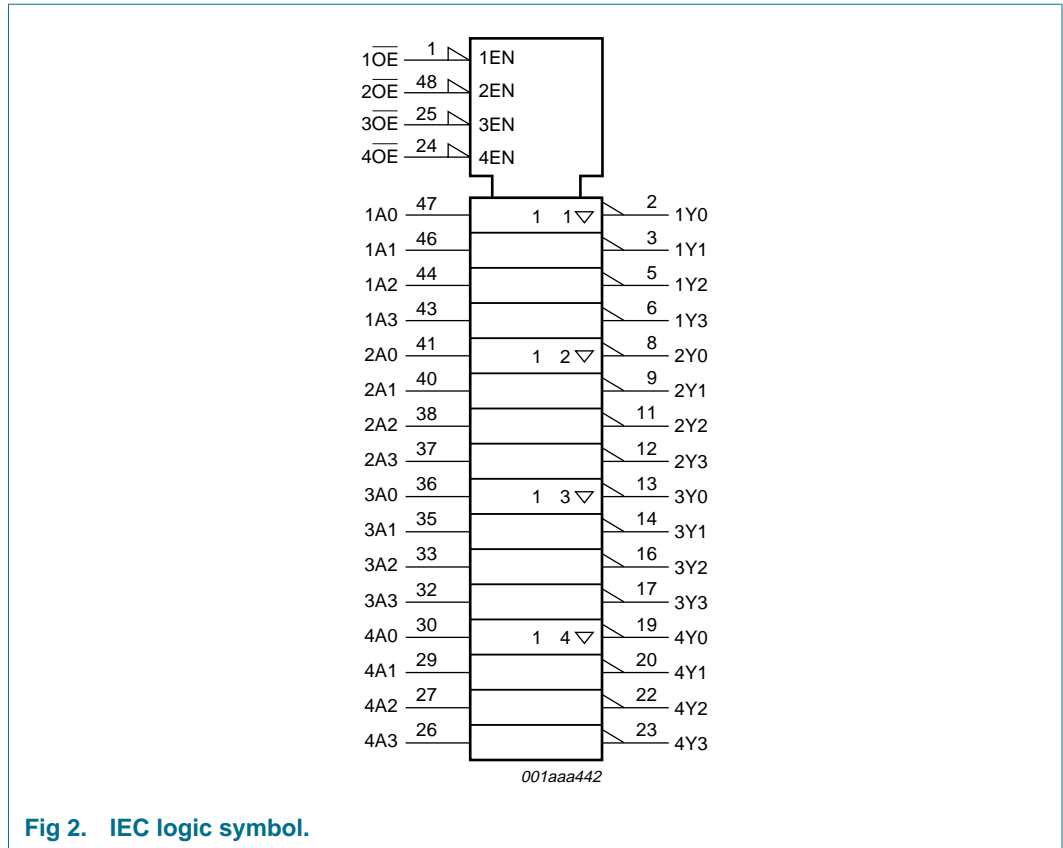


Fig 1. Logic symbol.



6. Pinning information

6.1 Pinning

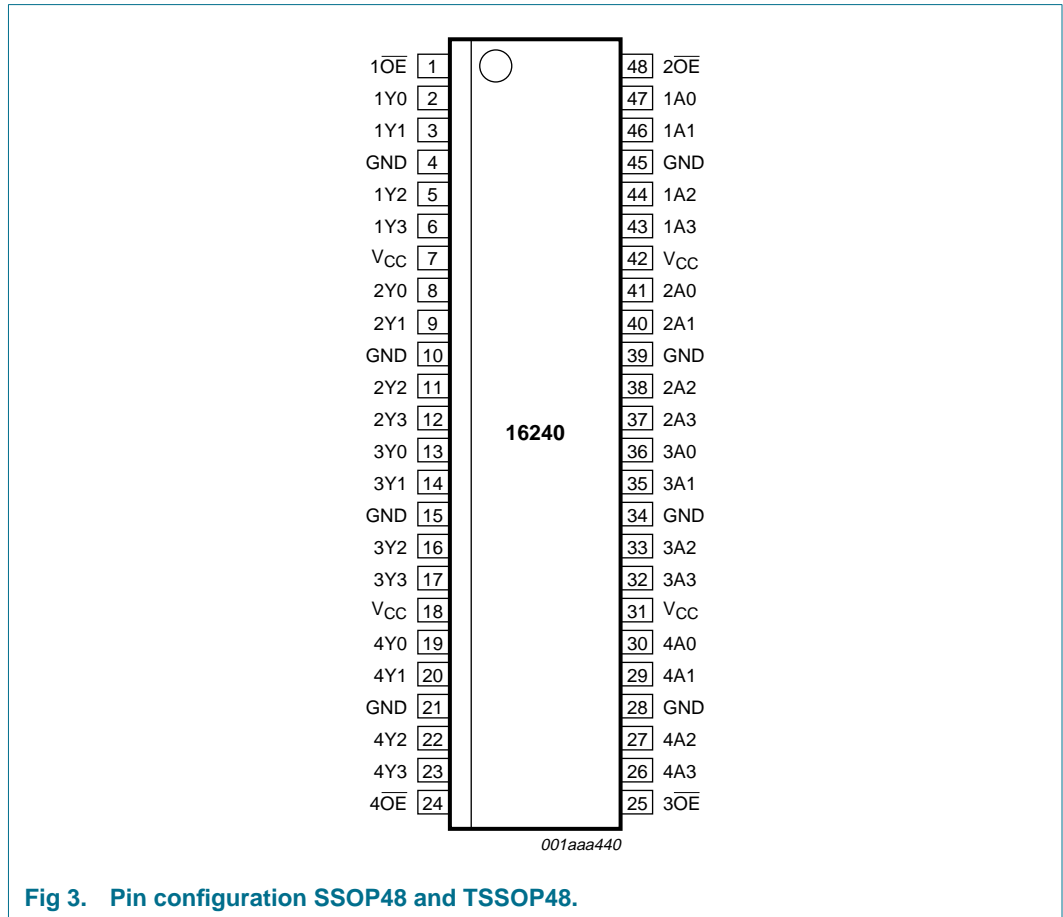


Fig 3. Pin configuration SSOP48 and TSSOP48.

6.2 Pin description

Table 3: Pin description

Pin	Symbol	Description
1	1OE	output enable input (active LOW)
2	1Y0	data output
3	1Y1	data output
4, 10, 15, 21, 28, 34, 39, 45	GND	ground (0 V)
5	1Y2	data output
6	1Y3	data output
7, 18, 31, 42	V _{CC}	supply voltage
8	2Y0	data output
9	2Y1	data output
11	2Y2	data output
12	2Y3	data output

Table 3: Pin description ...continued

Pin	Symbol	Description
13	3Y0	data output
14	3Y1	data output
16	3Y2	data output
17	3Y3	data output
19	4Y0	data output
20	4Y1	data output
22	4Y2	data output
23	4Y3	data output
24	4 $\overline{\text{OE}}$	output enable input (active LOW)
25	3 $\overline{\text{OE}}$	output enable input (active LOW)
26	4A3	data input
27	4A2	data input
29	4A1	data input
30	4A0	data input
32	3A3	data input
33	3A2	data input
35	3A1	data input
36	3A0	data input
37	2A3	data input
38	2A2	data input
40	2A1	data input
41	2A0	data input
43	1A3	data input
44	1A2	data input
46	1A1	data input
47	1A0	data input
48	2 $\overline{\text{OE}}$	output enable input (active LOW)

7. Functional description

7.1 Function table

Table 4: Function table [1]

Input		Output
n $\overline{\text{OE}}$	nAn	nYn
L	L	H
L	H	L
H	X	Z

- [1] H = HIGH voltage level;
 L = LOW voltage level;
 X = don't care;
 Z = high-impedance OFF-state.

8. Limiting values

Table 5: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+6.5	V
I_{IK}	input diode current	$V_I < 0$ V	-	-50	mA
V_I	input voltage		[1] -0.5	+6.5	V
I_{OK}	output diode current	$V_O > V_{CC}$ or $V_O < 0$ V	-	± 50	mA
V_O	output voltage	output HIGH or LOW state	[1] -0.5	$V_{CC} + 0.5$	V
		output 3-state	[1] -0.5	+6.5	V
I_O	output source or sink current	$V_O = 0$ V to V_{CC}	-	± 50	mA
I_{CC}, I_{GND}	V_{CC} or GND current		-	± 100	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	power dissipation	$T_{amb} = -40$ °C to +125 °C	[2] -	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] Above 60 °C the value of P_{tot} derates linearly with 5.5 mW/K.

9. Recommended operating conditions

Table 6: Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage	for maximum speed performance	2.7	-	3.6	V
		for low-voltage applications	1.2	-	3.6	V
V_I	input voltage		0	-	5.5	V
V_O	output voltage	output HIGH or LOW state	0	-	V_{CC}	V
		output 3-state	0	-	5.5	V
T_{amb}	operating ambient temperature	in free air	-40	-	+125	°C
t_r, t_f	input rise and fall times	$V_{CC} = 1.2$ V to 2.7 V	-	-	20	ns/V
		$V_{CC} = 2.7$ V to 3.6 V	-	-	10	ns/V

10. Static characteristics

Table 7: Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$T_{amb} = -40$ °C to +85 °C [1]						
V_{IH}	HIGH-level input voltage	$V_{CC} = 1.2$ V	V_{CC}	-	-	V
		$V_{CC} = 2.7$ V to 3.6 V	2.0	-	-	V

Table 7: Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{IL}	LOW-level input voltage	V _{CC} = 1.2 V	-	-	GND	V
		V _{CC} = 2.7 V to 3.6 V	-	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -100 μA; V _{CC} = 2.7 V to 3.6 V	V _{CC} - 0.2	V _{CC}	-	V
		I _O = -12 mA; V _{CC} = 2.7 V	V _{CC} - 0.5	-	-	V
		I _O = -18 mA; V _{CC} = 3.0 V	V _{CC} - 0.6	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 100 μA; V _{CC} = 2.7 V to 3.6 V	-	0	0.20	V
		I _O = 12 mA; V _{CC} = 2.7 V	-	-	0.40	V
		I _O = 24 mA; V _{CC} = 3.0 V	-	-	0.55	V
I _{LI}	input leakage current	V _I = 5.5 V or GND; V _{CC} = 3.6 V	-	±0.1	±5	μA
I _{OZ}	3-state output OFF-state current	V _I = V _{IH} or V _{IL} ; V _O = 5.5 V or GND; V _{CC} = 3.6 V	-	0.1	±5	μA
I _{off}	power-off leakage supply current	V _I or V _O = 5.5 V; V _{CC} = 0.0 V	-	0.1	±10	μA
I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 3.6 V	-	0.1	20	μA
ΔI _{CC}	additional quiescent supply current per input pin	V _I = V _{CC} - 0.6 V; I _O = 0 A; V _{CC} = 2.7 V to 3.6 V	-	5	500	μA
C _I	input capacitance		-	5.0	-	pF
T_{amb} = -40 °C to +125 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 1.2 V	V _{CC}	-	-	V
		V _{CC} = 2.7 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 1.2 V	-	-	GND	V
		V _{CC} = 2.7 V to 3.6 V	-	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -100 μA; V _{CC} = 2.7 V to 3.6 V	V _{CC} - 0.3	-	-	V
		I _O = -12 mA; V _{CC} = 2.7 V	V _{CC} - 0.65	-	-	V
		I _O = -18 mA; V _{CC} = 3.0 V	V _{CC} - 0.75	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 100 μA; V _{CC} = 2.7 V to 3.6 V	-	-	0.3	V
		I _O = 12 mA; V _{CC} = 2.7 V	-	-	0.6	V
		I _O = 24 mA; V _{CC} = 3.0 V	-	-	0.8	V
I _{LI}	input leakage current	V _I = 5.5 V or GND; V _{CC} = 3.6 V	-	-	±20	μA
I _{OZ}	3-state output OFF-state current	V _I = V _{IH} or V _{IL} ; V _O = 5.5 V or GND; V _{CC} = 3.6 V	-	-	±20	μA

Table 7: Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{off}	power-off leakage supply current	V_I or $V_O = 5.5$ V; $V_{CC} = 0.0$ V	-	-	± 20	μ A
I_{CC}	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 3.6$ V	-	-	80	μ A
ΔI_{CC}	additional quiescent supply current per input pin	$V_I = V_{CC} - 0.6$ V; $I_O = 0$ A; $V_{CC} = 2.7$ V to 3.6 V	-	-	5000	μ A

[1] All typical values are measured at $V_{CC} = 3.3$ V and $T_{amb} = 25$ °C.

11. Dynamic characteristics

Table 8: Dynamic characteristicsGND = 0 V; $t_r = t_f \leq 2.5$ ns; $C_L = 50$ pF; $R_L = 500$ Ω ; see [Figure 6](#).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$T_{amb} = -40$ °C to $+85$ °C [1]						
t_{PHL} , t_{PLH}	propagation delay nAn to nYn	see Figure 4 $V_{CC} = 1.2$ V $V_{CC} = 2.7$ V $V_{CC} = 3.0$ V to 3.6 V	- 1.0 [2] 1.0	12.0 - 2.8	- 5.2 4.2	ns ns ns
t_{PZH} , t_{PZL}	3-state output enable time nOE to nYn	see Figure 5 $V_{CC} = 1.2$ V $V_{CC} = 2.7$ V $V_{CC} = 3.0$ V to 3.6 V	- 1.5 [2] 1.0	18.0 - 3.5	- 5.8 5.0	ns ns ns
t_{PHZ} , t_{PLZ}	3-state output disable time nOE to nYn	see Figure 5 $V_{CC} = 1.2$ V $V_{CC} = 2.7$ V $V_{CC} = 3.0$ V to 3.6 V	- 1.5 [2] 1.5	11.0 - 3.9	- 5.1 4.9	ns ns ns
$t_{sk(0)}$	skew	$V_{CC} = 3.0$ V to 3.6 V	[3] -	-	1.0	ns
C_{PD}	power dissipation capacitance per gate	$V_{CC} = 3.3$ V outputs enabled outputs disabled	[4] [5] - -	12 4.0	- -	pF pF
$T_{amb} = -40$ °C to $+125$ °C						
t_{PHL} , t_{PLH}	propagation delay nAn to nYn	see Figure 4 $V_{CC} = 1.2$ V $V_{CC} = 2.7$ V $V_{CC} = 3.0$ V to 3.6 V	- 1.0 1.0	- - -	- 6.5 5.5	ns ns ns
t_{PZH} , t_{PZL}	3-state output enable time nOE to nYn	see Figure 5 $V_{CC} = 1.2$ V $V_{CC} = 2.7$ V $V_{CC} = 3.0$ V to 3.6 V	- 1.5 1.0	- - -	- 7.5 6.5	ns ns ns

Table 8: Dynamic characteristics ...continued
GND = 0 V; $t_r = t_f \leq 2.5$ ns; $C_L = 50$ pF; $R_L = 500$ Ω ; see [Figure 6](#).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_{PHZ} , t_{PLZ}	3-state output disable time $n\overline{OE}$ to nYn	see Figure 5	-	-	-	ns
		$V_{CC} = 1.2$ V	-	-	-	ns
		$V_{CC} = 2.7$ V	1.5	-	6.5	ns
		$V_{CC} = 3.0$ V to 3.6 V	1.5	-	6.5	ns
$t_{sk(0)}$	skew	$V_{CC} = 3.0$ V to 3.6 V	[3] -	-	1.5	ns

- [1] All typical values are measured at $T_{amb} = 25$ °C.
- [2] These typical values are measured at $V_{CC} = 3.3$ V.
- [3] Skew between any two outputs of the same package switching in the same direction. This parameter is guaranteed by design.
- [4] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
 f_i = input frequency in MHz;
 f_o = output frequency in MHz;
 C_L = output load capacitance in pF;
 V_{CC} = supply voltage in V;
 N = total load switching outputs;
 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.
- [5] The condition is $V_i = GND$ to V_{CC} .

12. Waveforms

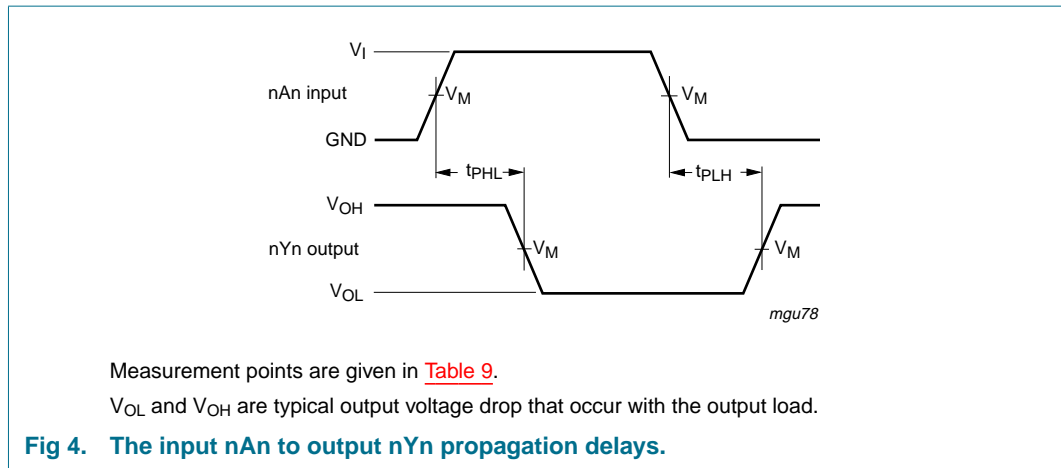


Table 9: Measurement points

Supply voltage	Input	Output
V_{CC}	V_M	V_M
1.2 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
2.7 V	1.5 V	1.5 V
3.0 V to 3.6 V	1.5 V	1.5 V

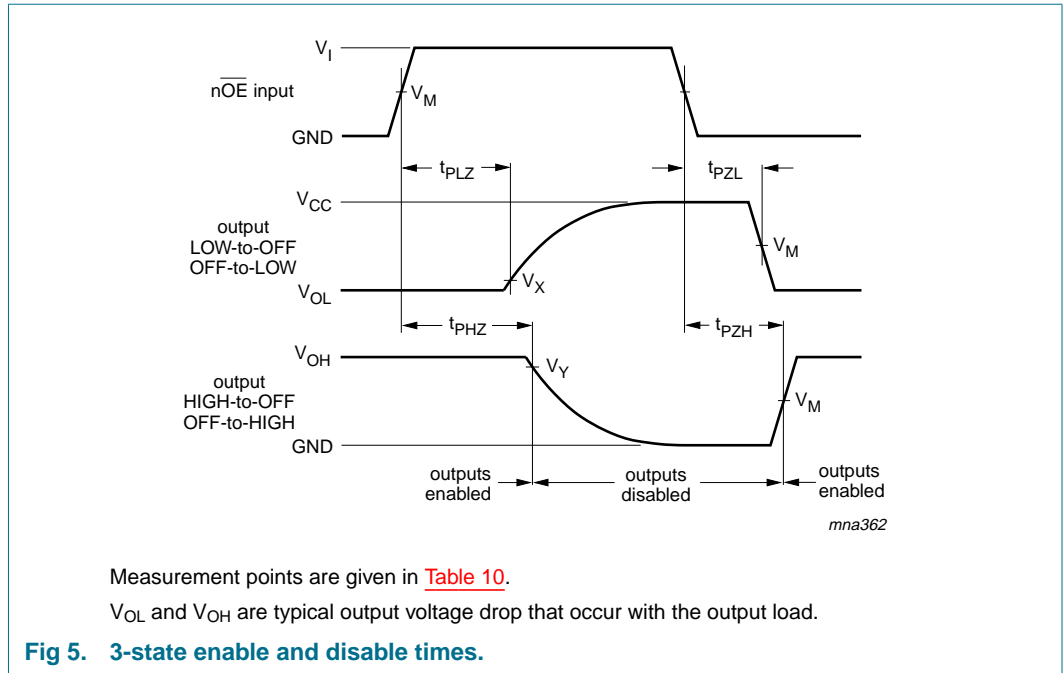


Table 10: Measurement points

Supply voltage	Input	Output		
		V_M	V_X	V_Y
1.2 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	$V_{OL} + 0.1 \text{ V}$	$V_{OH} - 0.1 \text{ V}$
2.7 V	1.5 V	1.5 V	$V_{OL} + 0.3 \text{ V}$	$V_{OH} - 0.3 \text{ V}$
3.0 V to 3.6 V	1.5 V	1.5 V	$V_{OL} + 0.3 \text{ V}$	$V_{OH} - 0.3 \text{ V}$

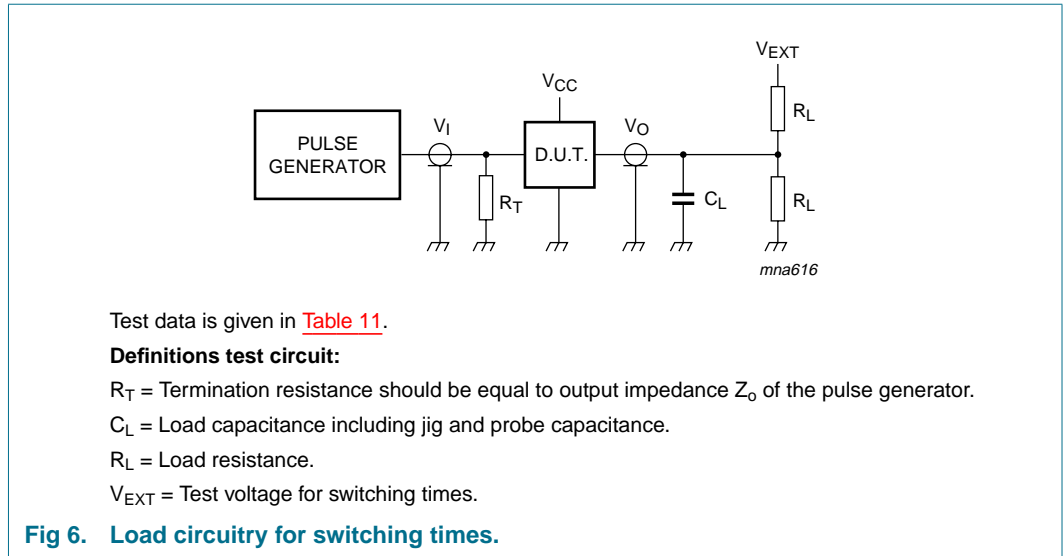


Table 11: Test data

Supply voltage	Input		Load		V_{EXT}		
V_{CC}	V_I	t_r, t_f	C_L	R_L	t_{PLH}, t_{PHL}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
1.2 V	V_{CC}	≤ 2.5 ns	50 pF	500 Ω [1]	open	GND	$2 \times V_{CC}$
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open	GND	$2 \times V_{CC}$
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open	GND	$2 \times V_{CC}$

[1] The circuit performs better when $R_L = 1000 \Omega$.

13. Package outline

TSSOP48: plastic thin shrink small outline package; 48 leads; body width 6.1 mm

SOT362-1

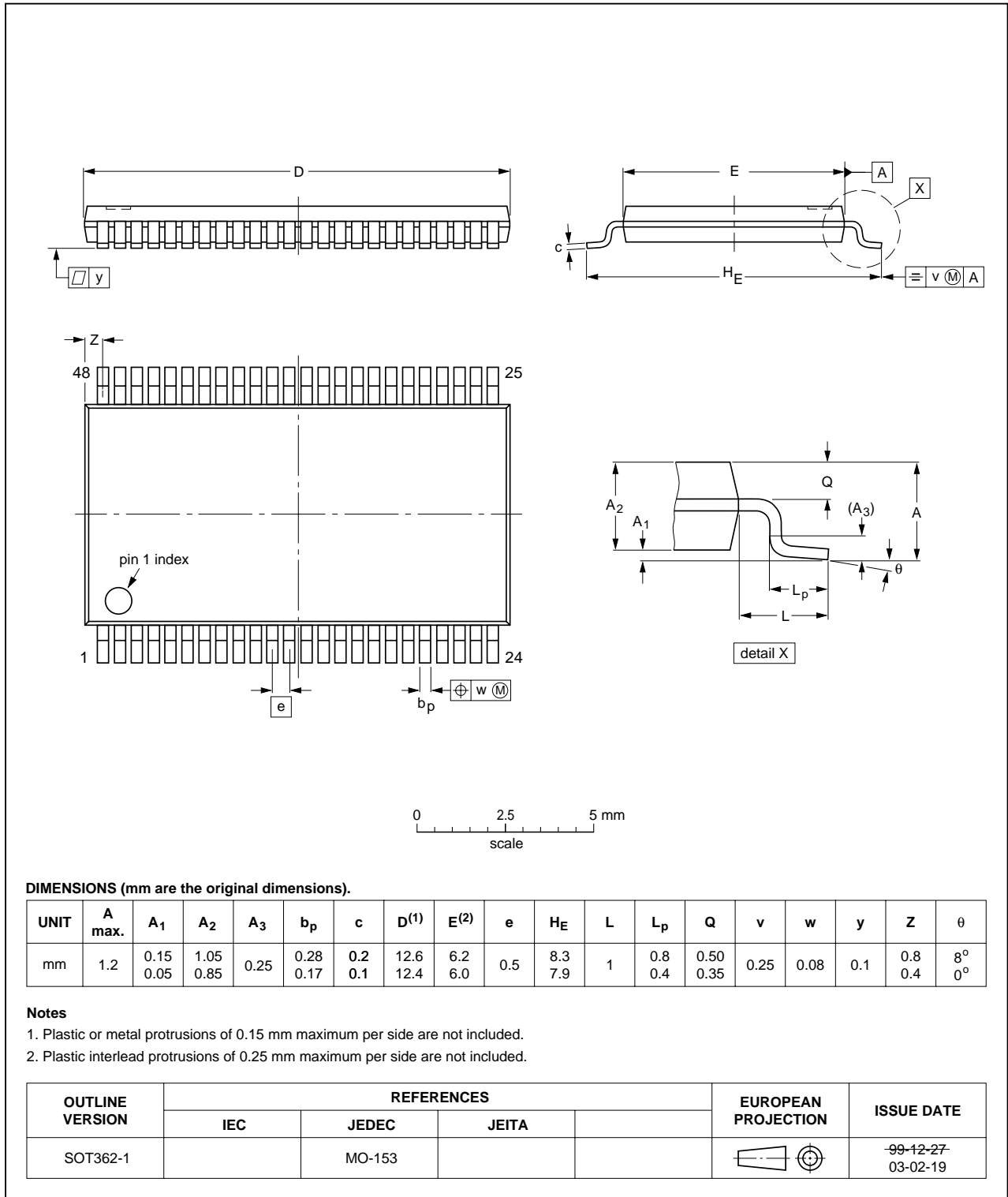


Fig 7. Package outline TSSOP48.

SSOP48: plastic shrink small outline package; 48 leads; body width 7.5 mm

SOT370-1

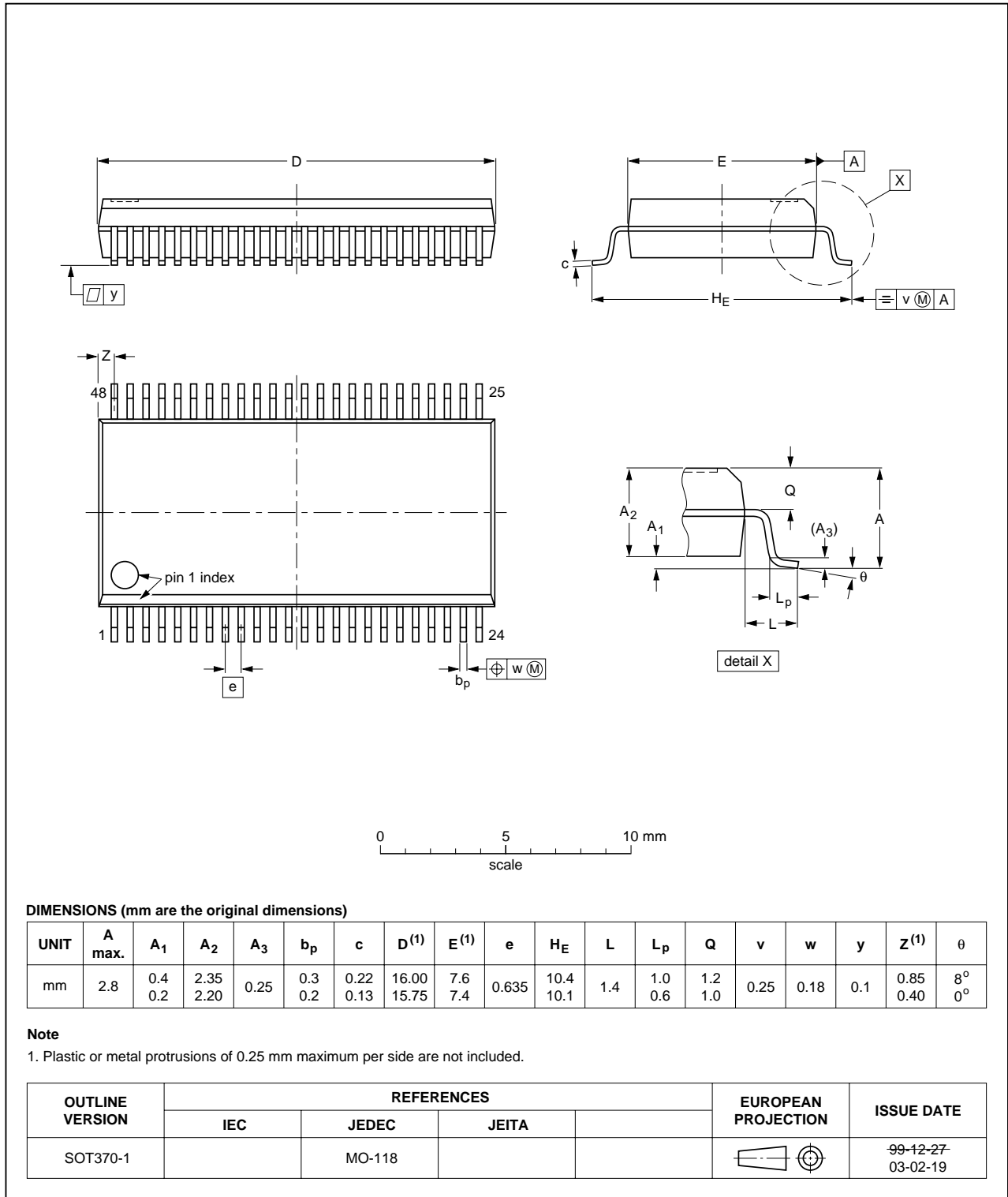


Fig 8. Package outline SSOP48.

14. Revision history

Table 12: Revision history

Document ID	Release date	Data sheet status	Change notice	Order number	Supersedes
74LVC16240A_3	20040305	Product data	-	9397 750 12871	74LVC16240A_2
Modifications:	<ul style="list-style-type: none"> The format of this data sheet has been redesigned to comply with the current presentation and information standard of Philips Semiconductors. Table 7: added values for $T_{amb} = -40\text{ °C}$ to $+125\text{ °C}$ Table 8: added values for $T_{amb} = -40\text{ °C}$ to $+125\text{ °C}$ 				
74LVC16240A_2	19970729	Product data	-	9397 750 04526	74LVC16240A_1
74LVC16240A_1	19951226	Product data	-	-	-

15. Data sheet status

Level	Data sheet status ^[1]	Product status ^[2] ^[3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.

[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

16. Definitions

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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19. Contents

1	General description	1
2	Features	1
3	Quick reference data	2
4	Ordering information	2
5	Functional diagram	3
6	Pinning information	5
6.1	Pinning	5
6.2	Pin description	5
7	Functional description	6
7.1	Function table	6
8	Limiting values	7
9	Recommended operating conditions	7
10	Static characteristics	7
11	Dynamic characteristics	9
12	Waveforms	10
13	Package outline	13
14	Revision history	15
15	Data sheet status	16
16	Definitions	16
17	Disclaimers	16
18	Contact information	16



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